

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

## Product Summary

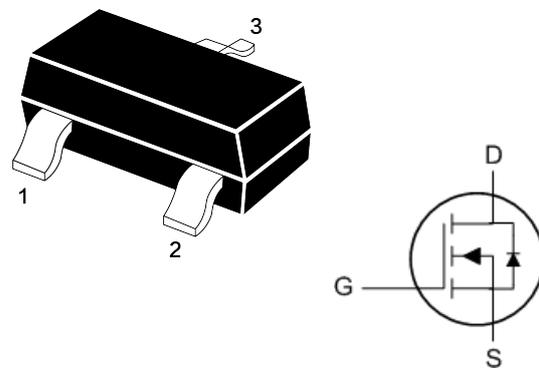


BVDSS	RDSON	ID
30V	12mΩ	7.0A

## Description

The JH3410L is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications. The JH3410L meet the RoHS and Green Product requirement with full function reliability approved.

## SOT-23-3L Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	7.0	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	5.5	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	29.4	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation <sup>3</sup>	2.0	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	---	85	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	---	$^\circ C/W$

## Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

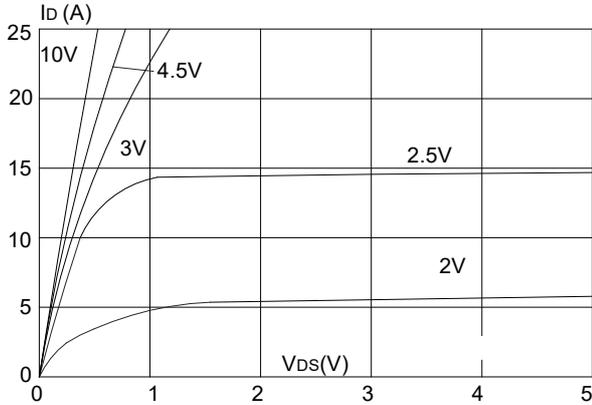
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V,	-	-	1.0	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V	-	-	±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.5	2.5	V
R <sub>DS(on)</sub>	Static Drain-Source on-Resistance <small>note3</small>	V <sub>GS</sub> =10V, I <sub>D</sub> =10A	-	12	17	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	-	17	25	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1.0MHz	-	614	-	pF
C <sub>oss</sub>	Output Capacitance		-	118	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	98	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =15V, I <sub>D</sub> =11A, V <sub>GS</sub> =10V	-	16	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	2.7	-	nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge		-	4.5	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =15V, R <sub>L</sub> =1.35Ω, R <sub>GEN</sub> =3Ω, V <sub>GS</sub> =10V	-	6	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	10	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time		-	30	-	ns
t <sub>f</sub>	Turn-off Fall Time		-	6.5	-	ns
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	7	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	30	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =15A	-	-	1.2	V
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =11A, di/dt=500A/μs	-	7	-	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge		T <sub>J</sub> =25°C	-	10	-

## Diode Characteristics

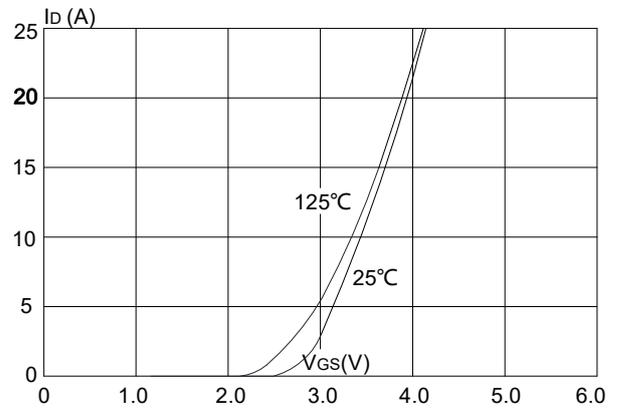
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	7	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =8A, di/dt=100A/μs, T <sub>J</sub> =25°C	---	8	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	2.9	---	nC

Note :

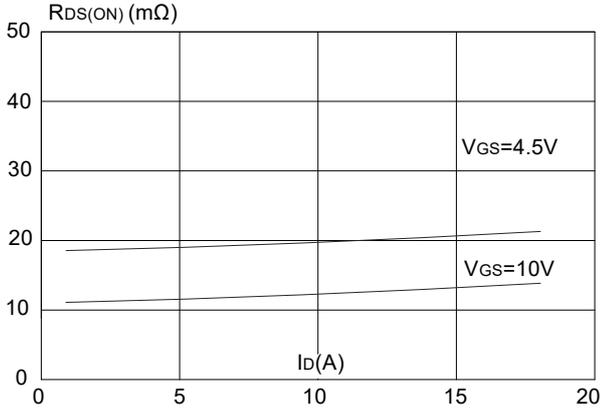
**Figure 1: Output Characteristics**



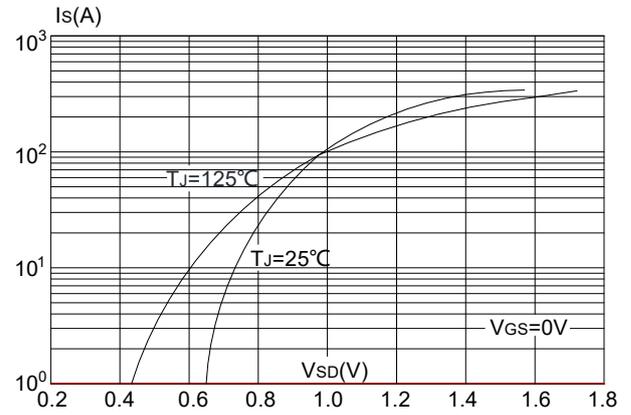
**Figure 2: Typical Transfer Characteristics**



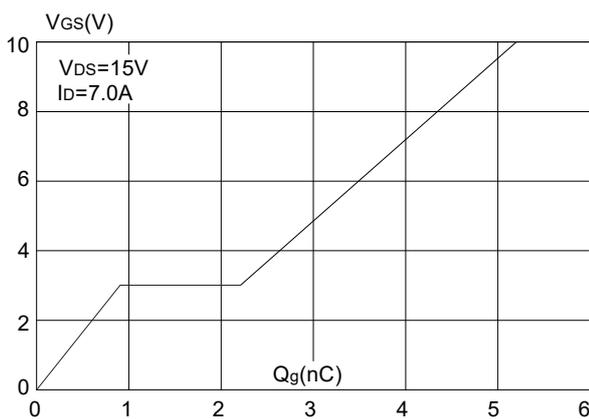
**Figure 3: On-resistance vs. Drain Current**



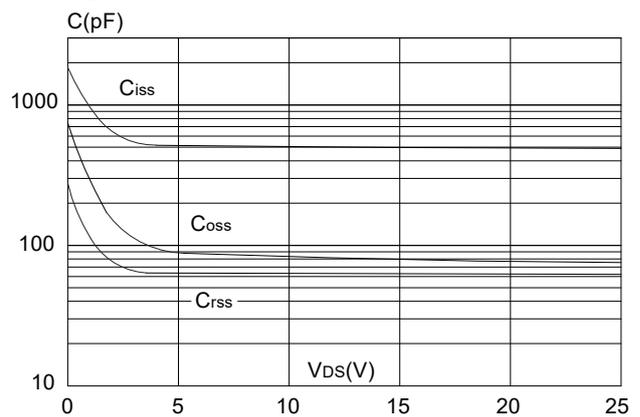
**Figure 4: Body Diode Characteristics**



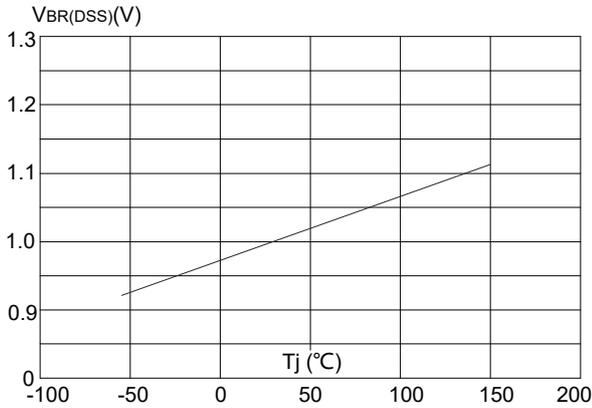
**Figure 5: Gate Charge Characteristics**



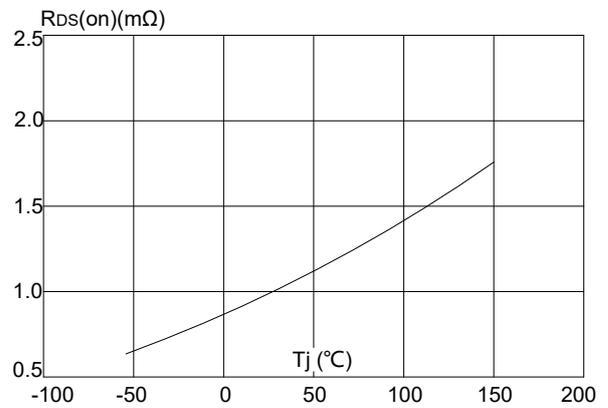
**Figure 6: Capacitance Characteristics**



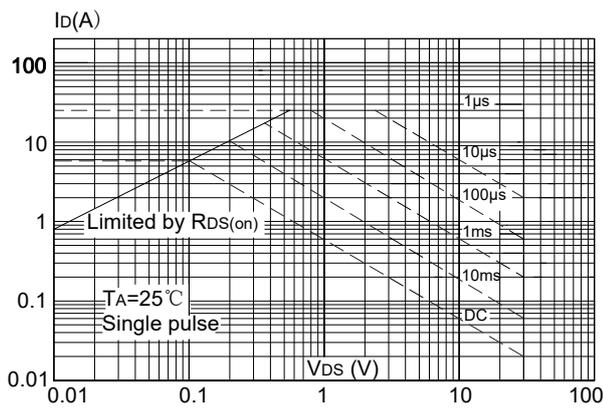
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



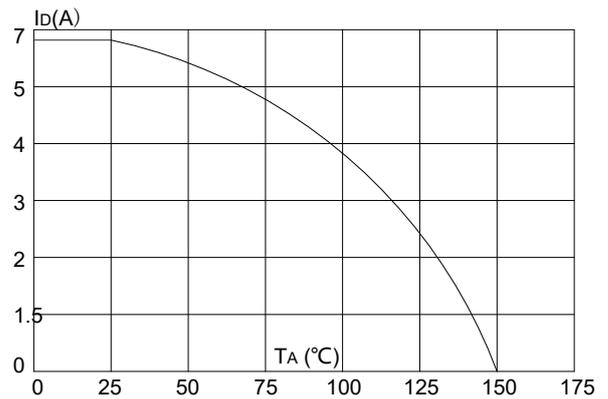
**Figure 8:** Normalized on Resistance vs. Junction Temperature



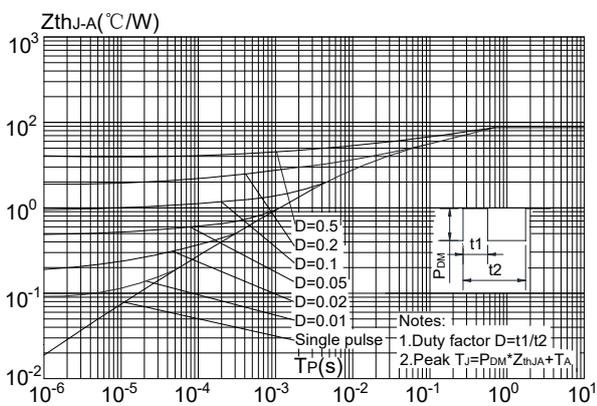
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature

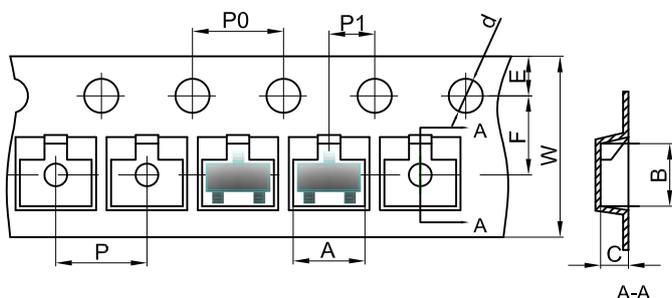


**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



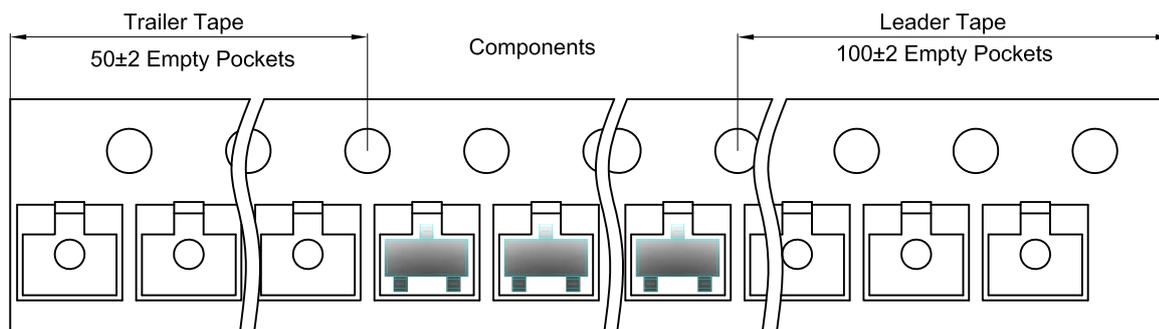
## SOT-23-3L Tape and Reel

### SOT-23-3L Embossed Carrier Tape

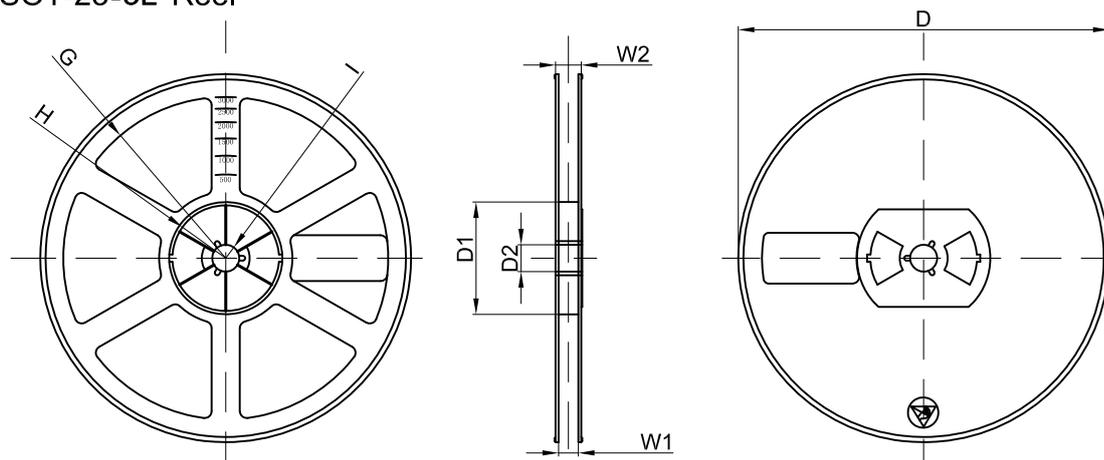


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

### SOT-23-3L Tape Leader and Trailer

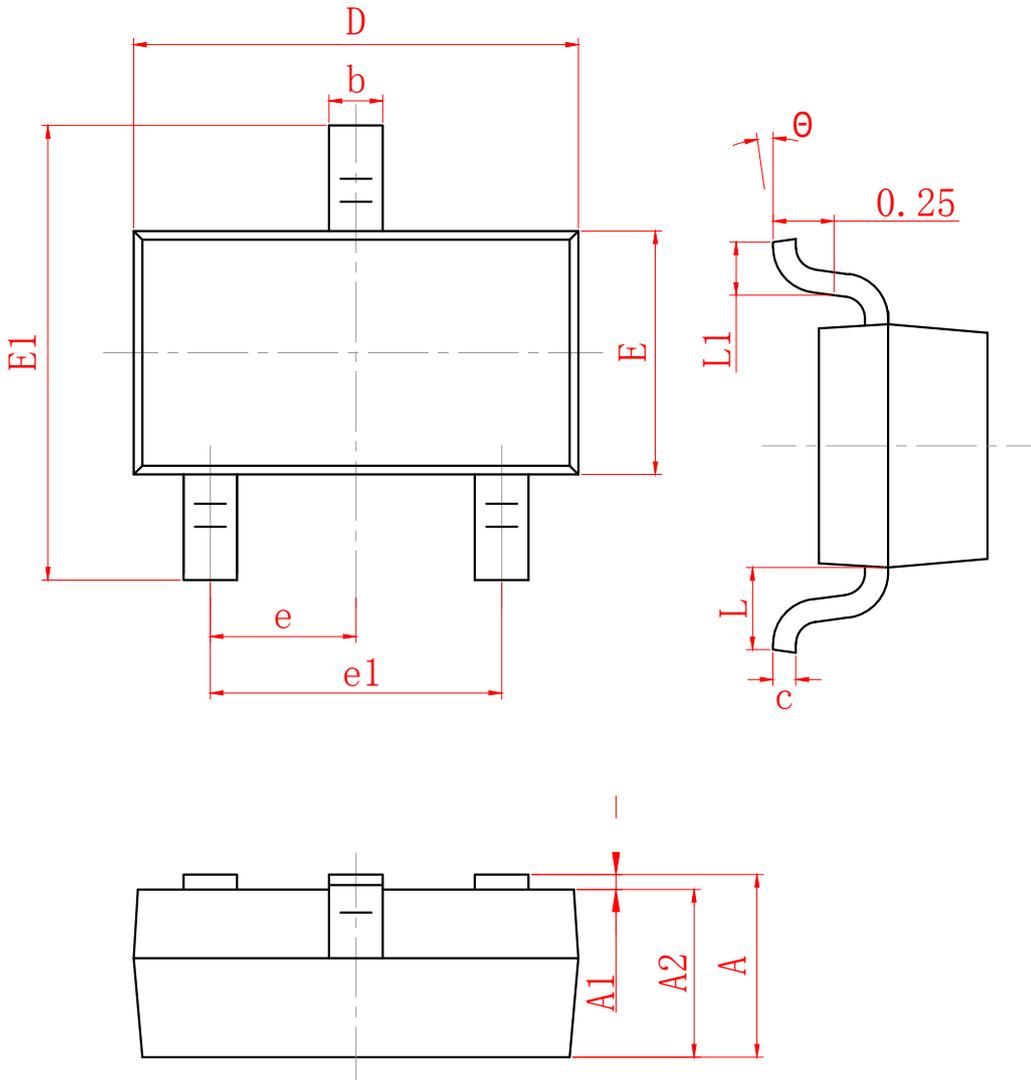


### SOT-23-3L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	45,000 pcs	203×203×195	180,000 pcs	438×438×220	



SYMBOL	MILLIMETER	
	MIN	MAX
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950 TYP	
e1	1.800	2.000
L	0.550 REF	
L1	0.300	0.500
$\theta$	0°	8°

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